

RELIABILITY REPORT FOR

DS2405, Rev B2

Dallas Semiconductor

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Prepared by:

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Conclusion:

The following qualification successfully meets the quality and reliability standards required of all Dallas Semiconductor products and processes:

In addition, Dallas Semiconductor's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

Device Description:

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

```
AfT = exp((Ea/k)*(1/Tu - 1/Ts)) = tu/ts

AfT = Acceleration factor due to Temperature

tu = Time at use temperature (e.g. 55°C)

ts = Time at stress temperature (e.g. 125°C)

k = Boltzmann's Constant (8.617 x 10-5 eV/°K)

Tu = Temperature at Use (°K)

Ts = Temperature at Stress (°K)
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Ea = Activation Energy (e.g. 0.7 ev)

temperature to the use ambient temperature.

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

```
AfV = exp(B*(Vs - Vu))

AfV = Acceleration factor due to Voltage

Vs = Stress Voltage (e.g. 7.0 volts)

Vu = Maximum Operating Voltage (e.g. 5.5 volts)

B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)
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The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

```
Fr = X/(ts * AfV * AfT * N * 2)
X = Chi-Sq statistical upper limit
N = Life test sample size
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Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE: MTTF (YRS): 72843 FITS: 1.6

The parameters used to calculate this failure rate are as follows:

Cf: 60% Ea: 0.7 B: 0 Tu: 25 °C Vu: 5.5 Volts

The reliability data follows. A the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available.

Device Information:

Process: 1P, 1M, 0.6um, Pd, Ti/TiN M1 , WJ BPSG

Passivation: Laser/TEOS Ox - Pass/Nit - Gen.LaserPrb

Die Size: 53 x 34

Number of Transistors: 0

Interconnect: Aluminum / 1% Silicon / 0.5% Copper

Gate Oxide Thickness: 150 Å

OPERATING LIFE						
DESCRIPTION	DATE COD	E CONDITION	REAL	POINT	QUANTITY	FAILS
INFANT LIFE	9740	125C, 6.0 VOLTS	48	HRS	770	0
HIGH VOLTAGE LIFE	9740	125C, 6.0 VOLTS	1000	HRS	116	0
INFANT LIFE	9749	125C, 6.0 VOLTS	48	HRS	770	0
HIGH VOLTAGE LIFE	9749	125C, 6.0 VOLTS	1500	HRS	116	0
HIGH VOLTAGE LIFE	9822	125C, 6.0 VOLTS	1000	HRS	256	0
				Total:		
TEMPERATURE CYCLE						
DESCRIPTION	DATE COD	E CONDITION	REAL	POINT	QUANTITY	FAILS
TEMP CYCLE	9740	-55C TO 125C	1000	CYS	77	0
TEMP CYCLE	9749	-55C TO 125C	1000	CYS	77	0
				Total:		
TEMPERATURE HUMIDITY BIAS						
DESCRIPTION	DATE COD	E CONDITION	REAL	READPOINT QUANTITY I		FAILS
BIASED MOISTURE	9740	85/85, 5.5 VOLTS	959	HRS	77	0
BIASED MOISTURE	9749	85/85, 5.5 VOLTS	959	HRS	77	0
				Total:		0
UNBIASED MOISTURE RESISTANCE						
DESCRIPTION	DATE COD	E CONDITION	REAL	READPOINT QUANTITY		FAILS
AUTOCLAVE	9740	121C, 2 ATM STEAM, UNBIASED	168	HRS	45	0

AUTOCLAVE 9749 121C, 2 ATM STEAM, UNBIASED 168 HRS 45 0

Total: 0

FAILURE RATE: MTTF (YRS): 72843 FITS: 1.6